

HAT1065T

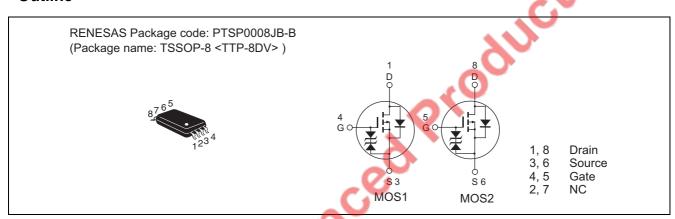
Silicon P Channel MOS FET High Speed Power Switching

REJ03G0161-0200 Rev.2.00 Aug 06, 2007

Features

- Low on-resistance
- Capable of –4 V gate drive
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|--|-----------------------------|-------------|------|
| Drain to source voltage | V_{DSS} | -200 | V |
| Gate to source voltage | V_{GSS} | ±15 | V |
| Drain current | I _D | -0.25 | А |
| Drain peak current | I _{D(pulse)} Note1 | -1 | А |
| Body-drain diode reverse drain current | I _{DR} | -0.25 | А |
| Channel dissipation | Pch Note2 | 1 | W |
| Channel dissipation | Pch Note3 | 1.5 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

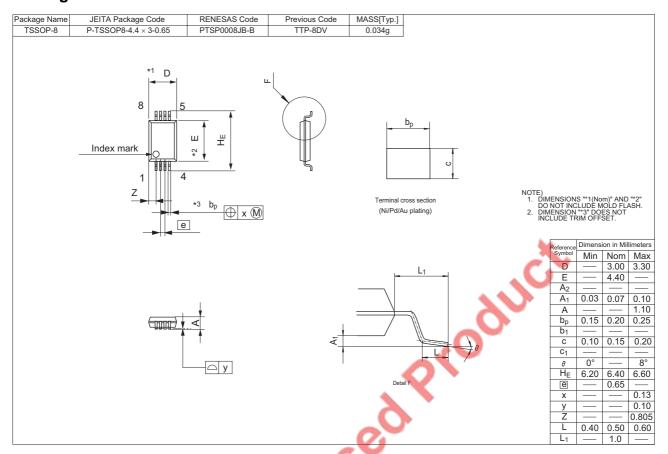
- 2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s
- 3. 2 Drive operation; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

| Drain to source breakdown voltage V _{(BRICSS} = -200 — — V I _D = -10 mA, V _{OS} = 0 Gate to source breakdown voltage V _{(BRICSS} ±115 — — V I _D = ±100 μA, V _{OS} = 0 Gate to source leak current I _{DSS} — — ±10 μA V _{OS} = ±12 V, V _{OS} = 0 Gate to source cutoff voltage V _{OS(of)} — — — 5 μA V _{DS} = 10 V, I _{DS} = 0 Gate to source cutoff voltage V _{OS(of)} — — — — 4 μA V _{DS} = 10 V, I _{DS} = 0 Gate to source cutoff voltage V _{OS(of)} — — — — 0.0 V V _{DS} = -10 V, I _{DS} = 0 Gate to source cutoff voltage V _{OS(of)} — — — — 0.0 V V _{DS} = -10 V, I _{DS} = -0.25 A, V _{DS} = 0 Gate to source cutoff voltage V _{OS(of)} — — — — 0.0 0.0 I _D = -0.25 A, V _{DS} = -0 0 0 I _D = -0.25 A, V _{DS} = -10 V, I _{DS} = -0.25 A, V _{DS} = -10 V, I _{DS} = -0.25 A, V _{DS} = -10 V, I _{DS} = -0.25 A, V _{DS} = -10 V, I _{DS} = -0.25 A, V _{DS} = | Item | Symbol | Min | Тур | Max | Unit | Test Conditions |
|---|-----------------------------------|---------------------|------|------|------|------|--|
| Gate to source breakdown voltage V _{(BR)GSS} ±15 — — V I _G = ±100 μA, V _{DS} = 0 | Drain to source breakdown voltage | | | | _ | V | $I_D = -10 \text{ mA}, V_{GS} = 0$ |
| Gate to source leak current I _{GSS} | Gate to source breakdown voltage | | ±15 | _ | _ | V | $I_G = \pm 100 \ \mu A, \ V_{DS} = 0$ |
| | Gate to source leak current | 1 | _ | _ | ±10 | μΑ | · · |
| | | _ | _ | _ | | | |
| | Gate to source cutoff voltage | | -1.0 | _ | -2.0 | V | $V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$ |
| $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | Static drain to source on state | R _{DS(on)} | _ | 5.0 | 6.2 | Ω | $I_D = -0.25 \text{ A}, V_{GS} = -10 \text{ V}^{\text{Note4}}$ |
| $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | resistance | R _{DS(on)} | _ | 6.0 | 7.5 | Ω | |
| | | R _{DS(on)} | _ | 7.0 | 10.0 | Ω | $I_D = -1 \text{ A}, V_{GS} = -5 \text{ V}^{\text{Note4}}$ |
| | Forward transfer admittance | | 0.29 | 0.45 | _ | S | $I_D = -0.25 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note4}}$ |
| $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | Input capacitance | Ciss | _ | 140 | _ | pF | |
| | Output capacitance | Coss | | 37 | _ | pF | $V_{GS} = 0$ |
| Rise time t_f — 9 — ns $V_{DD} \triangleq -30 \text{ V}$ Turn-off delay time t_{f} — 15 — ns $E_{AD} = E_{AD} $ | Reverse transfer capacitance | Crss | | 10 | _ | pF | f = 1 MHz |
| Rise time $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | Turn-on delay time | t _{d(on)} | _ | 12 | _ | ns | $V_{GS} = -5 \text{ V}, I_D = -0.25 \text{ A}$ |
| | Rise time | 1 | _ | 9 | _ | ns | V _{DD} ≅ -30 V |
| Fall time | Turn-off delay time | t _{d(off)} | _ | 25 | _ | ns | |
| Notes: 4. Pulse test | Fall time | | _ | 15 | _ | ns | |
| Notes: 4. Pulse test | Body-drain diode forward voltage | V_{DF} | _ | -0.9 | -1.4 | V | $I_F = -0.25 \text{ A}, V_{GS} = 0^{\text{Note4}}$ |
| | | ann | ou | ace | | | |

Package Dimensions



Ordering Information

| Part No. | lo. Quantity | | Shipping Container | | | | |
|---------------|--------------|--|--------------------|--|--|--|--|
| HAT1065T-EL-E | 3000 pcs | | Taping | | | | |
| ann | | | | | | | |
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